

SE3205A
N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This type used advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge.

- High density cell design for ultra low $R_{DS(ON)}$
- Excellent package for good heat dissipation

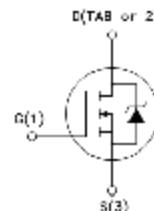
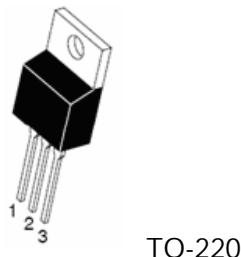
Features

For a single MOSFET

- $V_{DS} = 55V$
- $R_{DS(ON)} = 6.5m\Omega$ @ $V_{GS}=10V$
-

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	55	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	110	A
	Pulsed		390	
Total Power Dissipation	@ $TA=25^\circ C$	P_D	200	W
Operating Junction Temperature Range		T_J	-55 to 175	$^\circ C$

SE3205A

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250µA, V _{GS} =0V	55			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} =55V, V _{GS} =0V			100	µA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250µA	2.1		3.9	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =60A		6.5	7.9	mΩ
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz		3247		pF
C _{oss}	Output Capacitance			781		pF
C _{rss}	Reverse Transfer Capacitance			211		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =45V, I _D =62A			146	nC
Q _{gs}	Gate Source Charge				35	nC
Q _{gd}	Gate Drain Charge				54	nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =28V, R _{GEN} =4.5Ω		14		ns
t _{d(off)}	Turn-Off Delay Time			50		ns
t _{d(r)}	Turn-On Rise Time			101		ns
t _{d(f)}	Turn-Off Fall Time			65		ns

Typical Characteristics

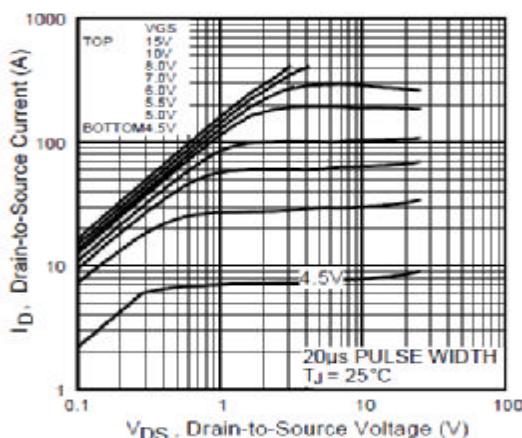


Fig 1. Typical Output Characteristics

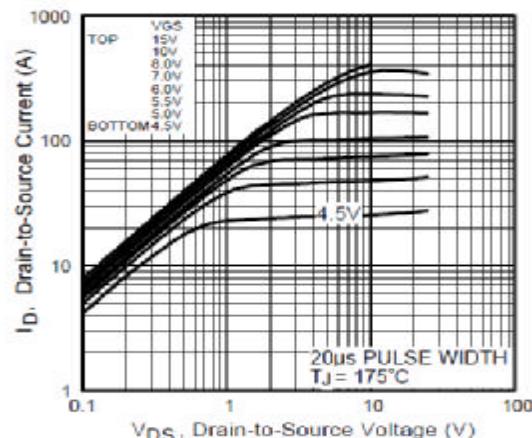


Fig 2. Typical Output Characteristics

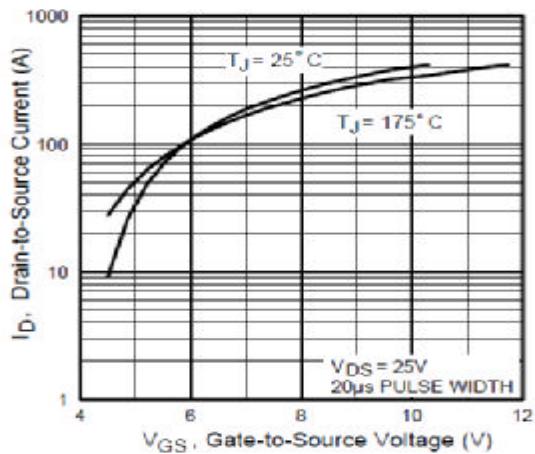


Fig 3. Typical Transfer Characteristics

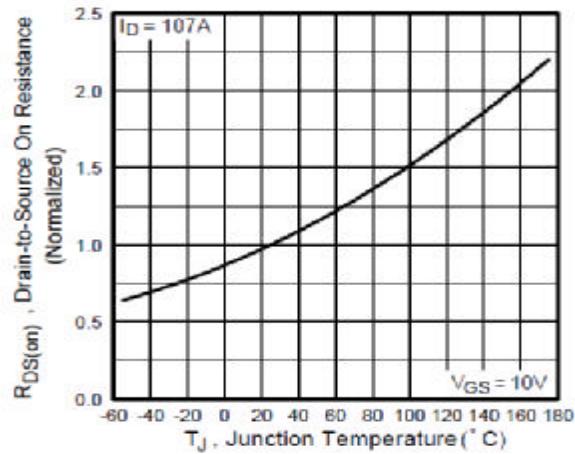


Fig 4. Normalized On-Resistance Vs. Temperature

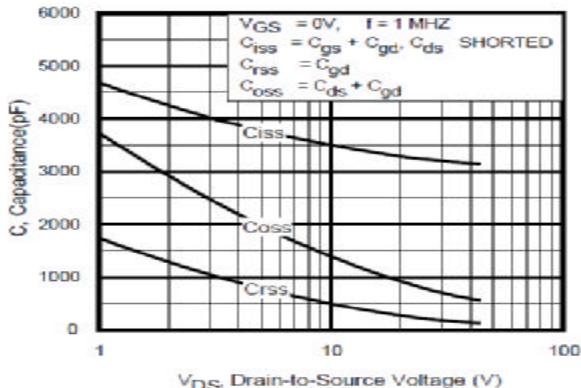


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

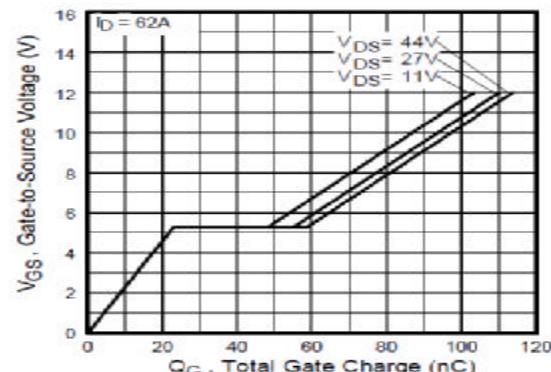


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

Typical Characteristics

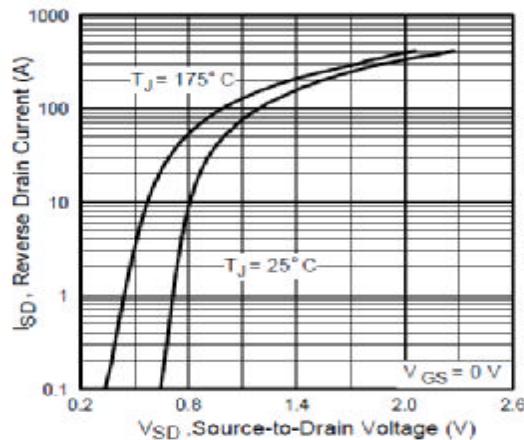


Fig 7. Typical Source-Drain Diode Forward Voltage

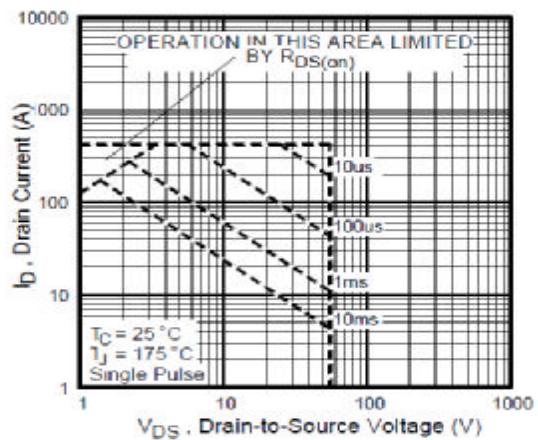


Fig 8. Maximum Safe Operating Area

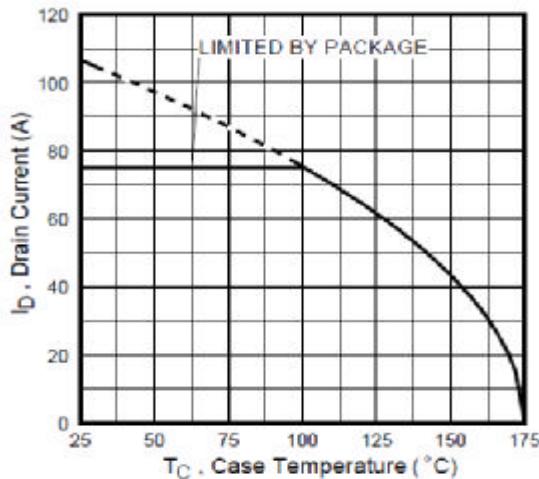


Fig 9. Maximum Drain Current Vs. Case Temperature

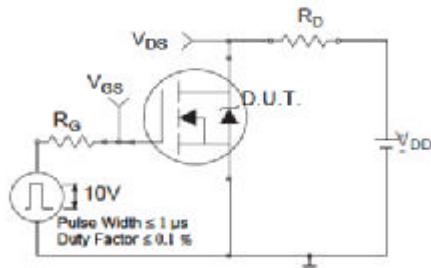


Fig 10a. Switching Time Test Circuit

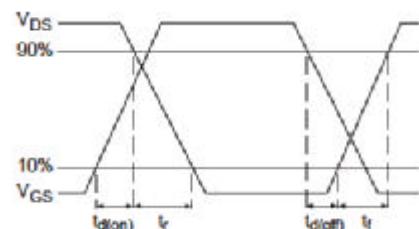
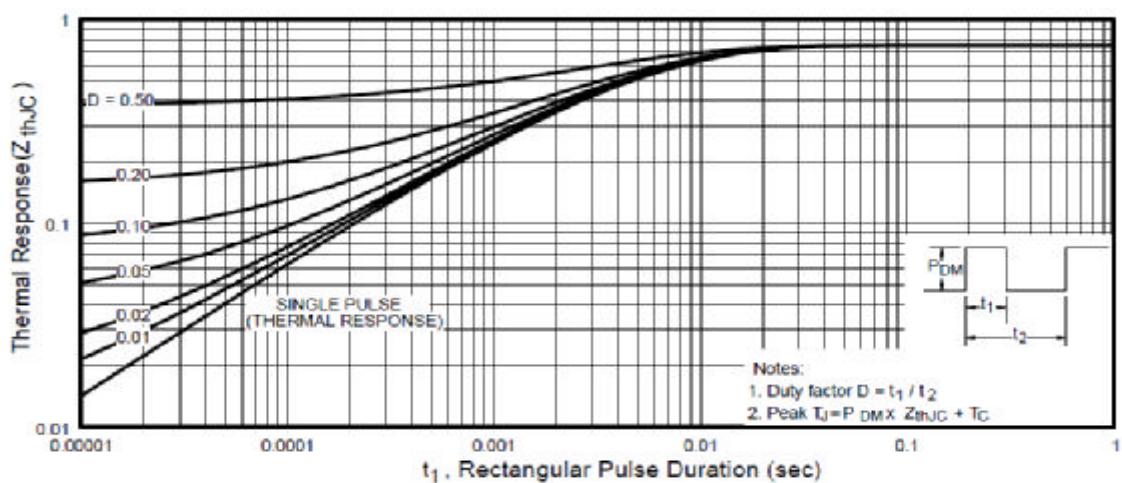
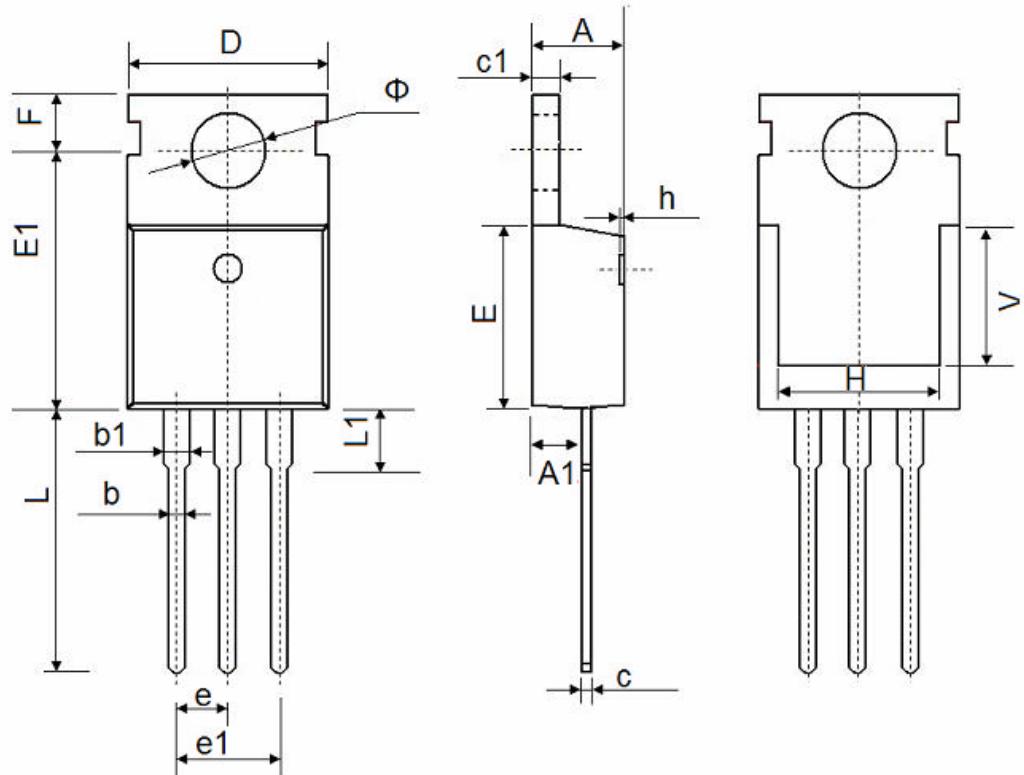


Fig 10b. Switching Time Waveforms



Package Outline Dimension

TO-220



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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